

SN75179B 差分驱动器和接收器对

1 特性

- 符合或超出 TIA/EIA-422-B、TIA/EIA-485-A 和 ITU Recommendation V.11 的要求
- 总线电压范围：-7V 至 12V
- 正负电流限制
- 驱动器输出能力：60mA (最大值)
- 驱动器热关断保护
- 接收器输入阻抗：12kΩ 最小值
- 接收器输入灵敏度：±200mV
- 接收器输入迟滞：50 mV (典型值)
- 由 5V 单电源供电
- 低功耗要求

2 说明

SN75179B 是一款差分驱动器和接收器对，专为平衡传输线路应用而设计，符合 TIA/EIA-422-B、TIA/EIA-485-A 和 ITU Recommendation V.11 的要求。该器件旨在提高长总线线路上全双工数据通信的性能。

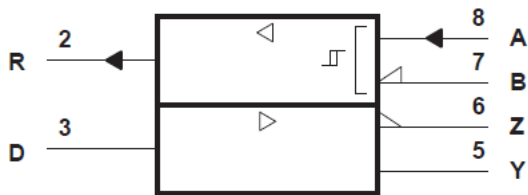
SN75179B 驱动器输出可限制正电流和负电流。该接收器具有高输入阻抗、用于改进抗扰度的输入迟滞，以及在 -7V 至 12V 共模输入电压范围内的 ±200mV 输入灵敏度。驱动器提供热关断以防止线路故障情况。热关断设计为在约 150°C 的结温下发生。SN75179B 旨在驱动高达 60mA 的电流负载。

SN75179B 的工作温度范围是 0°C 至 70°C。

封装信息

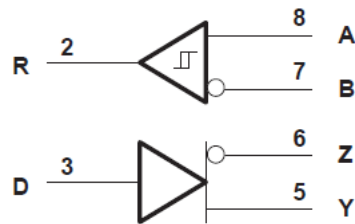
器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)
SN75179B	D (SOIC)	4.9 mm x 3.91 mm
	P (PDIP)	9.81 mm x 9.43 mm
	PS (SOP)	6.2 mm x 5.3 mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



A. 此符号符合 ANSI/IEEE 标准 91-1984 和 IEC 出版物 617-12。

逻辑符号



逻辑图 (正逻辑)



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3 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision E (June 2008) to Revision F (October 2022)	Page
• 将数据表格式更改为最新的数据表格式.....	1
• Changed the <i>Thermal Information</i> table.....	4

4 Pin Configuration and Functions

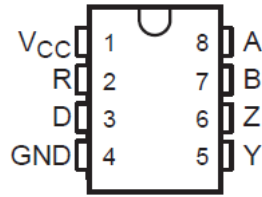


图 4-1. D, PS, or P Package
Top View

表 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1	V _{CC}	P	5V Voltage Supply
2	R	O	RS485 Logic Output
3	D	I	RS485 Logic Input
4	GND	G	Ground
5	Y	O	Non-Inverting RS485 Bus Output
6	Z	O	Inverted RS485 Bus Output
7	B	I	Inverted RS485 Bus Input
8	A	I	Non-Inverting RS485 Bus Input

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾		7	V
	Voltage range at any bus terminal	- 10	15	V
V _{ID}	Differential input voltage ⁽³⁾		±25	V
T _{stg}	Storage temperature	- 65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to network ground terminal.
- (3) Differential input voltage is measured at the noninverting input with respect to the corresponding inverting input.

5.2 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		4.75	5	5.25	V
V _{IH}	High-level input voltage	Driver	2			V
V _{IL}	Low-level input voltage	Driver			0.8	V
V _{IC}	Common-mode input voltage		- 7 ⁽¹⁾		12	V
V _{ID}	Differential input voltage,				±12	V
I _{OH}	High level output current	Driver			- 602	mA
		Receiver			- 400	µA
I _{OL}	Low level output current	Driver			60	mA
		Receiver			8	mA
T _A	Operating free-air temperature		0		70	°C

- (1) The algebraic convention, where the less positive (more negative) limit is designated minimum, is used in this data sheet for common-mode input voltage and threshold voltage.

5.3 Thermal Information

THERMAL METRIC ⁽¹⁾		SOIC (D)	PDIP (P)	SOP (PS)	UNIT
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	116.7	109.5	84.3	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.3	53.9	65.4	
R _{θJB}	Junction-to-board thermal resistance	63.4	65.7	62.1	
ψ _{JT}	Junction-to-top characterization parameter	8.8	11.6	31.3	
ψ _{JB}	Junction-to-board characterization parameter	62.6	64.5	60.4	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

5.4 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IK}	Input clamp voltage	I _I = -18 mA				-1.5	V
V _O	Output voltage	I _O = 0		0		6	V
V _{OD1}	Differential output voltage	I _O = 0		1.5		6	V
V _{OD2}	Differential output voltage	R _L = 100 Ω	See 图 6-1	1/2 V _{OD1}			V
		R _L = 54 Ω	See 图 6-1	1.5	2.5	5	
V _{OD3}	Differential output voltage	See ⁽⁴⁾		1.5		5	V
Δ V _{OD}	Change in magnitude of differential output voltage					±0.2	V
V _{OC}	Common mode output voltage	R _L = 54 Ω or 100 Ω,	See 图 6-1			3	V
						-1	
Δ V _{OC}	Change in magnitude of common-mode output voltage ⁽³⁾					±0.2	V
I _O	Output current	V _{CC} = 0	V _O = -7 V to 12 V			±100	μA
I _{IH}	High-level input current	V _{IH} = 2.4 V				20	μA
I _{IL}	Low-level input current	V _{IL} = 0.4 V				-200	μA
I _{OS}	Short circuit output current	V _O = -7 V				-250	mA
		V _O = V _{CC}				250	
		V _O = 12 V				250	
I _{CC}	Supply current (total package)	No load			57	70	mA

(1) All typical values are at V_{CC} = 5 V and T_A = 25°C.

(2) The minimum V_{OD2} with 100-Ω load is either 1/2 V_{OD2} or 2 V, whichever is greater

(3) Δ|V_{OD}| and Δ|V_{OC}| are the changes in magnitude of V_{OD} and V_{OC}, respectively, that occur when the input is changed from a high level to a low level.

(4) See TIA/EIA-485-A, Figure 3.5, Test Termination Measurement 2.

5.5 Switching Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{d(OD)}	Differential output delay time R _L = 54 Ω, See 图 6-3		15	22	ns
t _{t(OD)}	Differential output transition time R _L = 54 Ω, See 图 6-3		20	30	ns

5.6 Symbol Equivalent

DATA-SHEET PARAMETER	TIA/EIA-422-B	TIA/EIA-485-A
V _O	V _{oa} , V _{ob}	V _{oa} , V _{ob}
V _{OD1}	V _o	V _o
V _{OD2}	V _t (R _L = 100 Ω)	V _t (R _L = 54 Ω)
V _{OD3}		V _t (Test Termination Measurement 2)
D V _{OD}	V _t - V̄ _t	V _t - V̄ _t
V _{OC}	V _{os}	V _{os}
D V _{OC}	V _{os} - V̄ _{os}	V _{os} - V̄ _{os}
I _{OS}	I _{sa} , I _{sb}	
I _O	I _{xa} , I _{xb}	I _{ia} , I _{ib}

5.7 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	$V_O = 2.7\text{ V}$	$I_O = -0.4\text{ mA}$				0.2	V
V_{IT-}	Negative-going input threshold voltage	$V_O = 0.5\text{ V}$	$I_O = 8\text{ mA}$		0.2 ⁽²⁾			V
$V_{hys }$	Hysteresis voltage ($V_{IT+} - V_{IT-}$)					50		mV
V_{OH}	High-level output voltage	$V_{ID} = 200\text{ mV}$	$I_{OH} = -400\text{ }\mu\text{A}$	See 图 6-2	2.7			V
V_{OL}	Low-level output voltage	$V_{ID} = -200\text{ mV}$	$I_{OL} = 8\text{ mA}$	See 图 6-2			0.45	V
I_I	Line input current	Other input at 0 V	See ⁽³⁾	$V_I = 12\text{ V}$			1	mA
				$V_I = -7\text{ V}$			-0.8	mA
r_I	Input resistance				12			k Ω
I_{OS}	Short-circuit output current				-15		-85	mA
I_{OS}	Supply current (total package)	No load				57	70	mA

(1) All typical values are at $V_{CC} = 5\text{ V}$ and $T_A = 25^\circ\text{C}$.

(2) The algebraic convention, where the less positive (more negative) limit is designated minimum, is used in this data sheet for common-mode input voltage and threshold voltage levels only.

(3) See TIA/EIA-422-B for exact conditions.

5.8 Switching Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V}$				19	35	ns
t_{PHL}	Propagation delay time, high- to low-level output	$C_L = 15\text{ pF}$	See 图 6-4			30	40	ns

5.9 Typical Characteristics

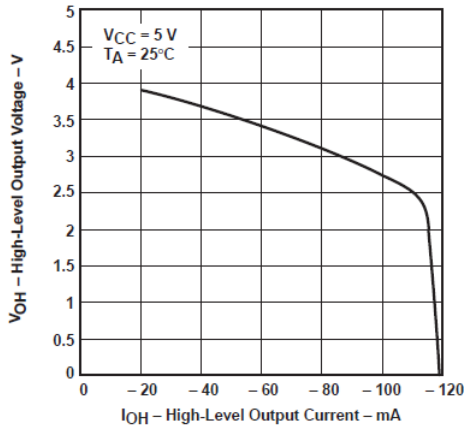


图 5-1. Driver High-Level Output Voltage vs High-Level Output Current

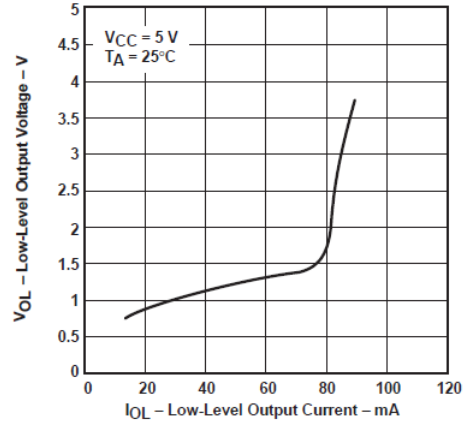


图 5-2. Driver Low-Level Output Voltage vs Low-Level Output Current

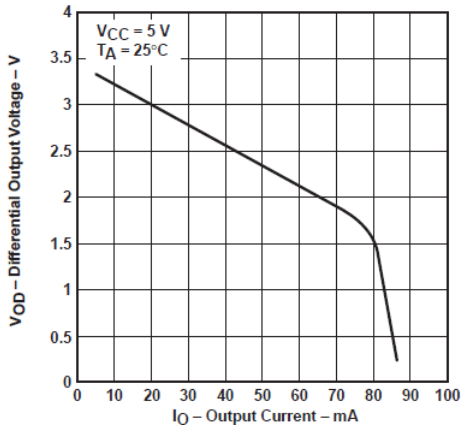


图 5-3. Driver Differential Output Voltage vs Output Current

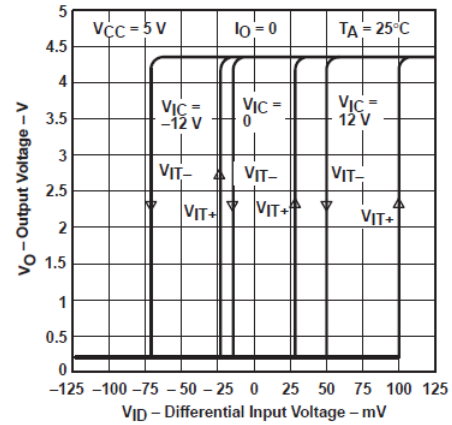


图 5-4. Receiver Output Voltage vs Differential Input Voltage

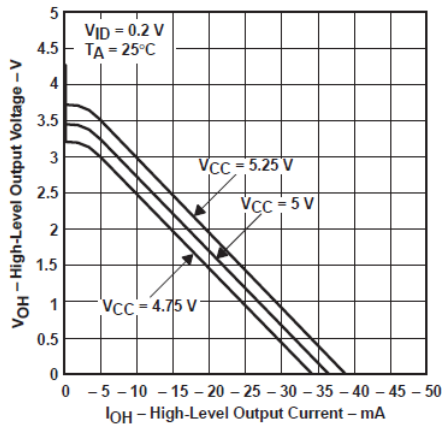


图 5-5. High-Level Output Voltage vs High-Level Output Current

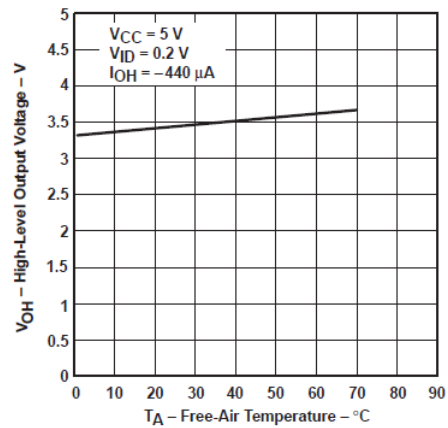


图 5-6. High-Level Output Voltage vs Free-Air Temperature

5.9 Typical Characteristics (continued)

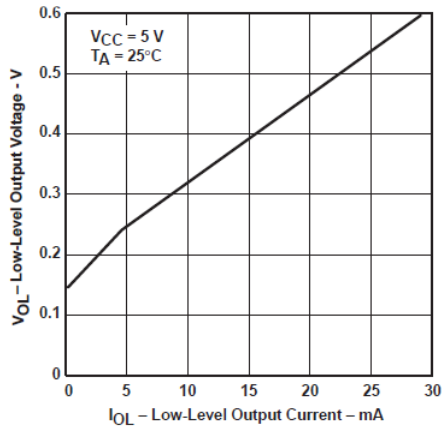


图 5-7. Receiver Low-Level Output Voltage vs Low-Level Output Current

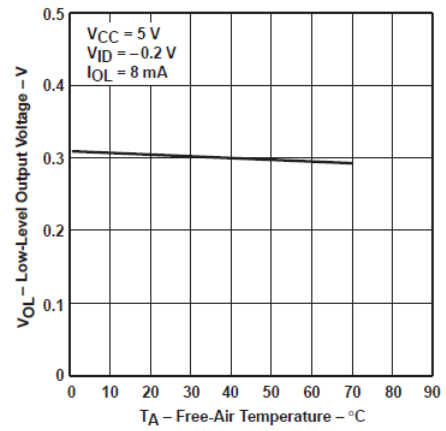


图 5-8. Receiver Low-Level Output Voltage vs Free-Air Temperature

6 Parameter Measurement Information

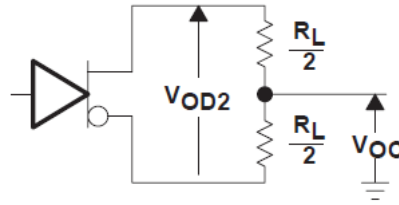


图 6-1. Driver V_{DD} and V_{OC}

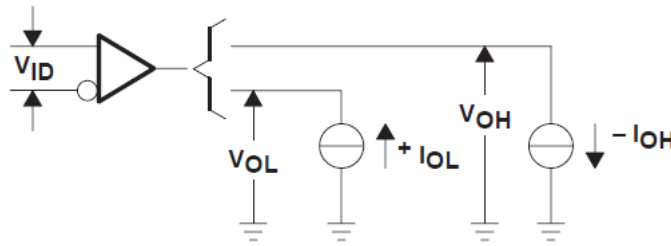
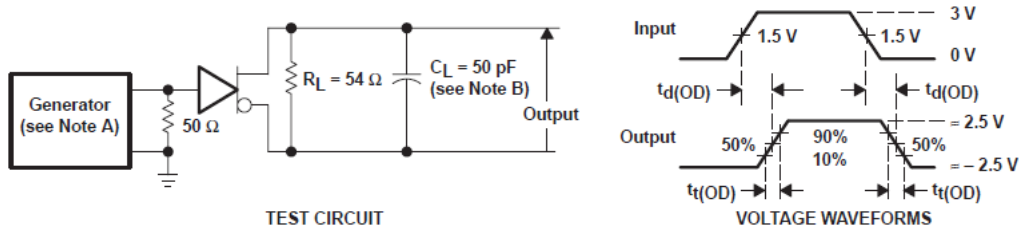
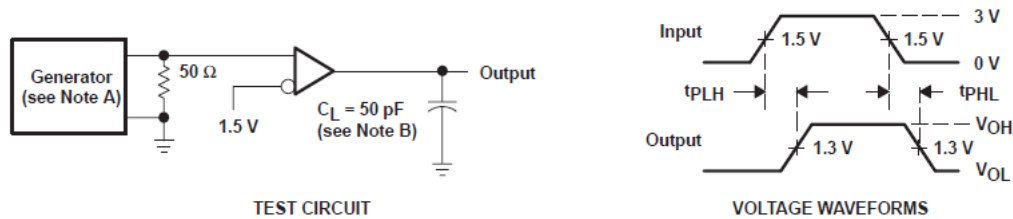


图 6-2. Receiver V_{OH} and V_{OL}



- A. The input pulse is supplied by a generator having the following characteristics: $PRR \leq 1$ MHz, 50% duty cycle, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

图 6-3. Driver Test Circuit and Voltage Waveforms

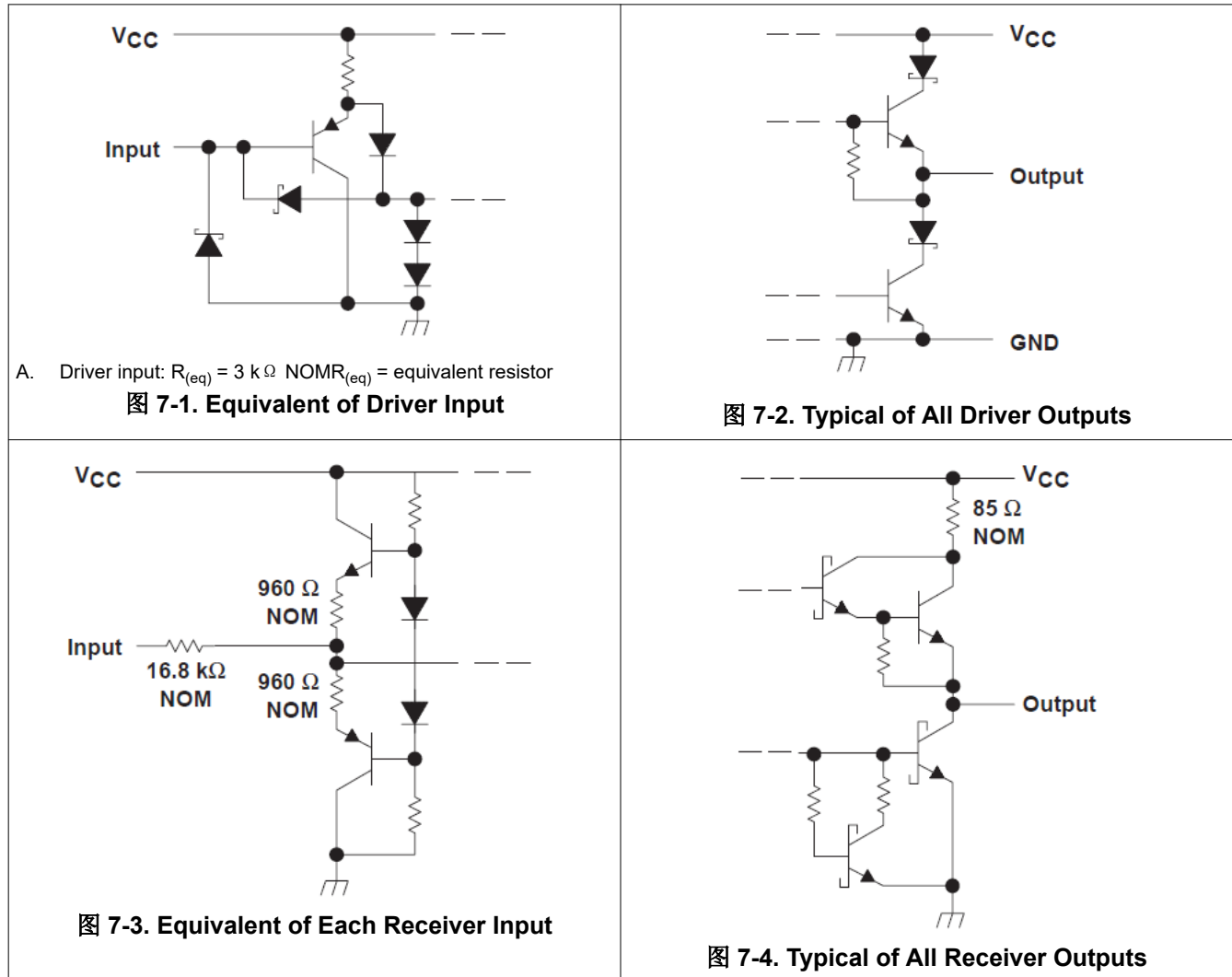


- A. The input pulse is supplied by a generator having the following characteristics: $PRR \leq 1$ MHz, 50% duty cycle, $t_r \leq 6$ ns, $t_f \leq 6$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

图 6-4. Receiver Test Circuit and Voltage Waveforms

7 Detailed Description

7.1 Functional Block Diagram



7.2 Device Functional Modes

表 7-1. Driver⁽¹⁾

INPUT D	OUTPUTS	
	Y	Z
H	H	L
L	L	H

(1) H = high level, L = low level, ? = indeterminate

表 7-2. Receiver⁽¹⁾

DIFFERENTIAL INPUTS A - B	OUTPUT R
$V_{ID} \geq 0.2\text{ V}$	H
$-0.2\text{ V} < V_{ID} < 0.2\text{ V}$?
$V_{ID} \leq -0.2\text{ V}$	L
Open	?

(1) H = high level, L = low level, ? = indeterminate

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 Documentation Support

8.1.1 Related Documentation

8.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.3 支持资源

[TI E2E™ 支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

8.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

8.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN75179BD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75179B	
SN75179BDE4	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75179B	
SN75179BDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75179B	Samples
SN75179BDRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75179B	Samples
SN75179BP	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75179BP	Samples
SN75179BPE4	ACTIVE	PDIP	P	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75179BP	Samples
SN75179BPSR	ACTIVE	SO	PS	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	A179B	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75179BDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN75179BPSR	SO	PS	8	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN75179BDR	SOIC	D	8	2500	340.5	336.1	25.0
SN75179BPSR	SO	PS	8	2000	356.0	356.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN75179BD	D	SOIC	8	75	507	8	3940	4.32
SN75179BDE4	D	SOIC	8	75	507	8	3940	4.32
SN75179BP	P	PDIP	8	50	506	13.97	11230	4.32
SN75179BPE4	P	PDIP	8	50	506	13.97	11230	4.32



D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $.006$ [0.15] per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
 EXPOSED METAL SHOWN
 SCALE:8X



SOLDER MASK DETAILS

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NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

PS (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - Falls within JEDEC MS-001 variation BA.

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